



BUK764R0-55B

N-channel TrenchMOS standard level FET

Rev. 5 — 22 April 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	55	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 ; see Figure 4	[1] -	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	300	W

Static characteristics

$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 7 ; see Figure 12	-	3.4	4	mΩ
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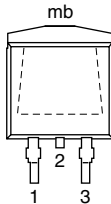
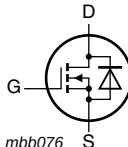
Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 55\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; unclamped	-	-	1.2	J
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $V_{DS} = 44\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$; see Figure 13	-	25	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain ^[1]		
3	S	source		
mb	D	mounting base; connected to drain		
SOT404 (D2PAK)				

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BUK764R0-55B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ;	[1] -	75	A
		see Figure 4	[2][3] -	193	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; see Figure 1	[1] -	75	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; see Figure 4	-	774	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$; see Figure 2	-	300	W
T_{stg}	storage temperature		-55	175	$^{\circ}\text{C}$
T_j	junction temperature		-55	175	$^{\circ}\text{C}$
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	[2][1] -	193	A
			[1] -	75	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$	-	774	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 55\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; unclamped	-	1.2	J
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	see Figure 3	[4][5][6][7] -	-	J

[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.

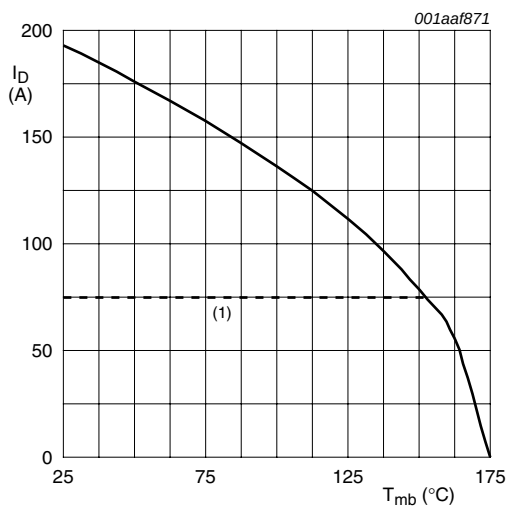
[3] Refer to document 9397 750 12572 for further information.

[4] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

[5] Single-pulse avalanche rating limited by maximum junction temperature of $175\text{ }^{\circ}\text{C}$.

[6] Repetitive avalanche rating limited by an average junction temperature of $170\text{ }^{\circ}\text{C}$.

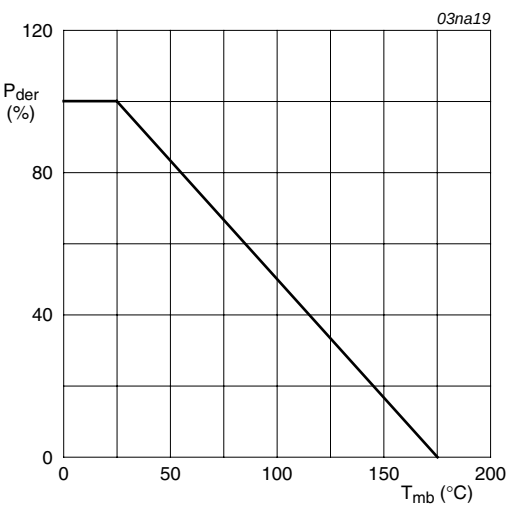
[7] Refer to application note AN10273 for further information.



$$V_{GS} \geq 10V$$

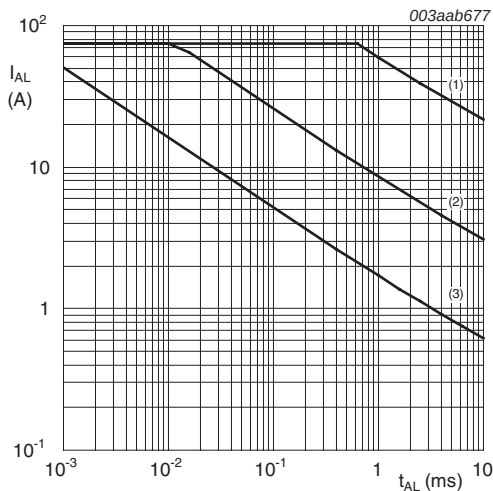
(1) Capped at 75 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature.



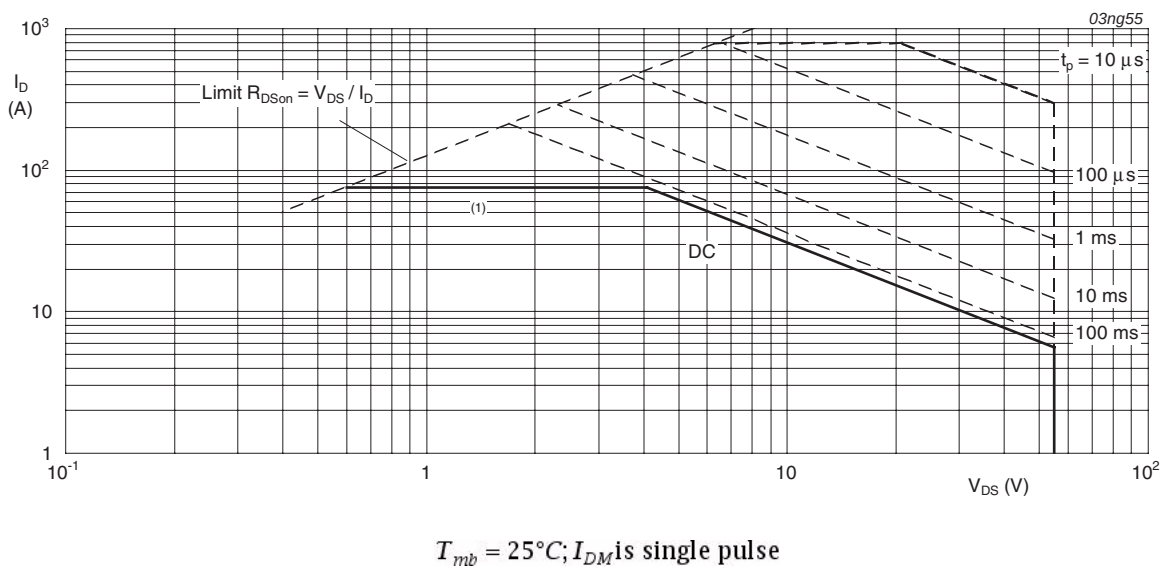
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



- (1) Single-pulse; $T_j = 25^{\circ}C$.
- (2) Single-pulse; $T_j = 150^{\circ}C$.
- (3) Repetitive

Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time.



(1) Capped at 75 A due to package.

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W

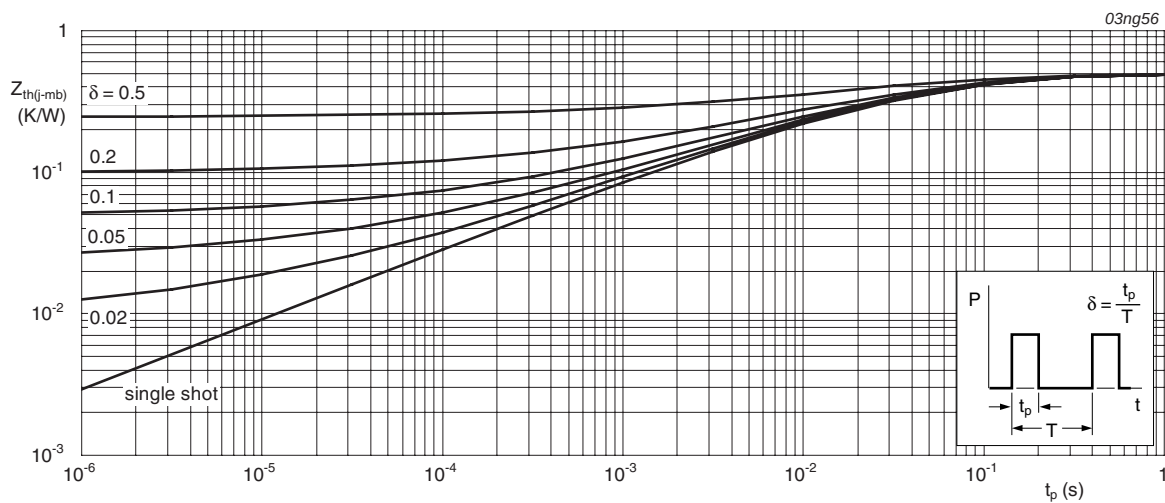
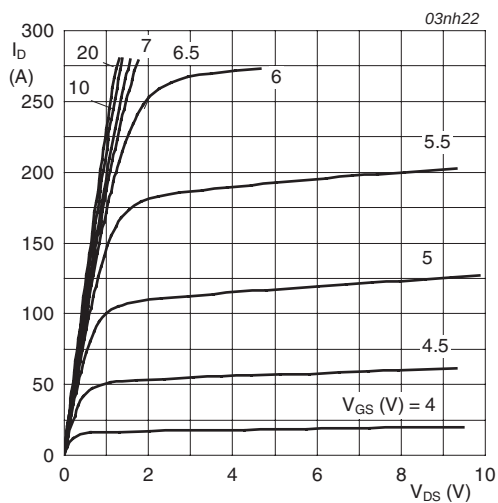


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

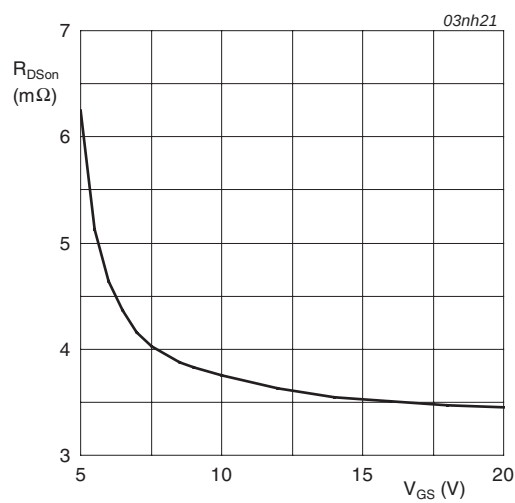
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _J = 25 °C	55	-	-	V
		I _D = 0.25 mA; V _{GS} = 0 V; T _J = -55 °C	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 25 °C; see Figure 11	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = -55 °C; see Figure 11	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 175 °C; see Figure 11	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _J = 175 °C	-	-	500	µA
		V _{DS} = 55 V; V _{GS} = 0 V; T _J = 25 °C	-	0.02	1	µA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _J = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _J = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _J = 175 °C; see Figure 7 ; see Figure 12	-	-	8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _J = 25 °C; see Figure 7 ; see Figure 12	-	3.4	4	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 44 V; V _{GS} = 10 V; T _J = 25 °C; see Figure 13	-	86	-	nC
Q _{GS}	gate-source charge		-	18	-	nC
Q _{GD}	gate-drain charge		-	25	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _J = 25 °C; see Figure 14	-	5082	6776	pF
C _{oss}	output capacitance		-	1054	1265	pF
C _{rss}	reverse transfer capacitance		-	450	617	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V; R _{G(ext)} = 10 Ω; T _J = 25 °C	-	23	-	ns
t _r	rise time		-	51	-	ns
t _{d(off)}	turn-off delay time		-	71	-	ns
t _f	fall time		-	41	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; T _J = 25 °C	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; T _J = 25 °C	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; T _J = 25 °C	-	7.5	-	nH
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 40 A; V _{GS} = 0 V; T _J = 25 °C; see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/µs; V _{GS} = -10 V; V _{DS} = 30 V; T _J = 25 °C	-	95	-	ns
Q _r	recovered charge		-	251	-	nC



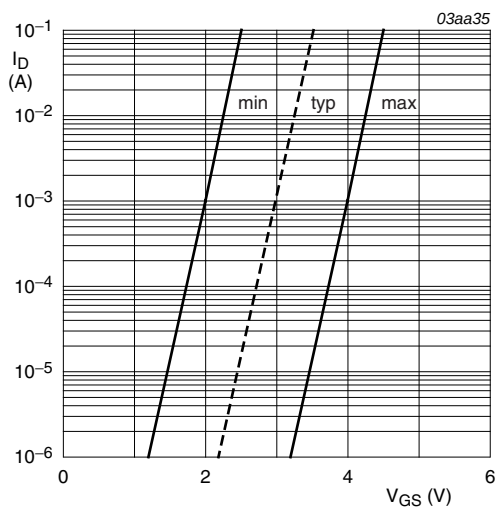
$T_j = 25^{\circ}\text{C}; t_p = 300\mu\text{s}$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



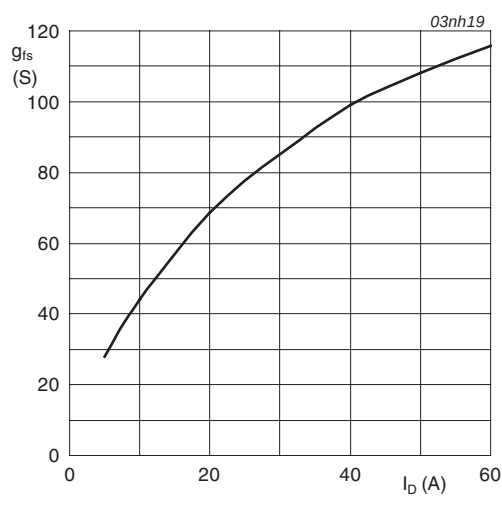
$T_j = 25^{\circ}\text{C}; I_D = 25\text{A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



$T_j = 25^{\circ}\text{C}; V_{DS} = 5\text{V}$

Fig 8. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25^{\circ}\text{C}; V_{DS} = 25\text{V}$

Fig 9. Forward transconductance as a function of drain current; typical values

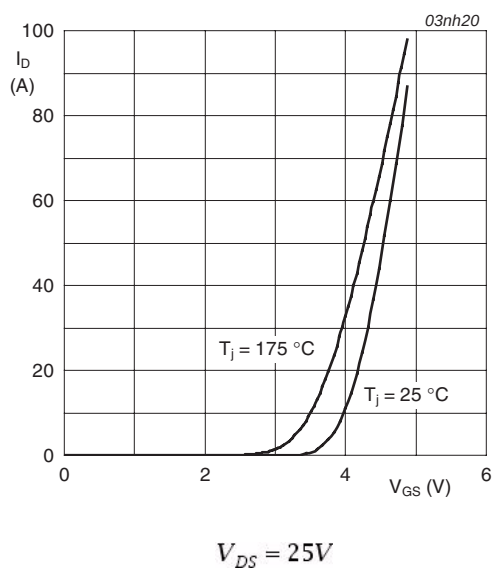


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

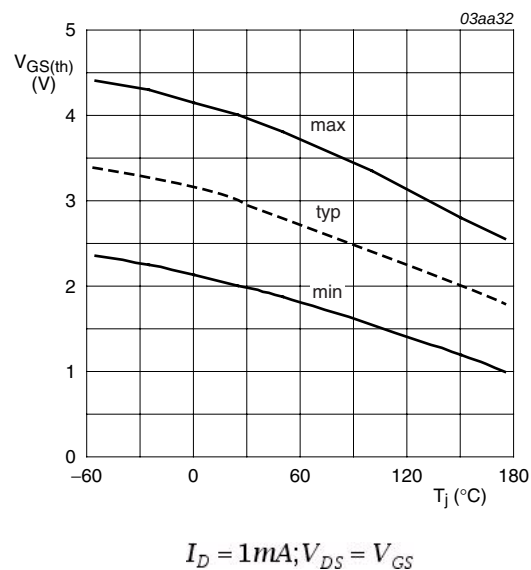


Fig 11. Gate-source threshold voltage as a function of junction temperature

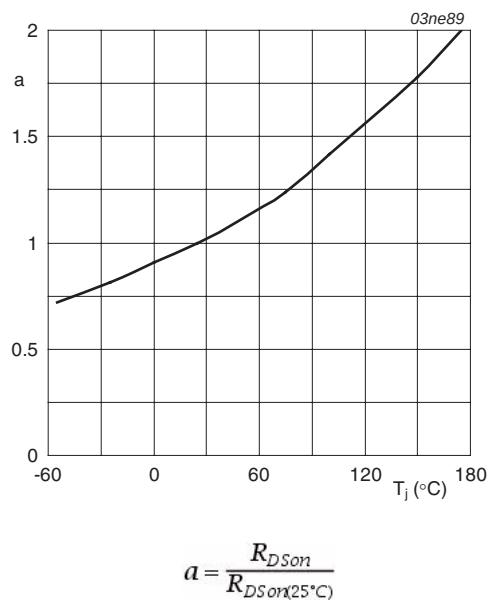


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

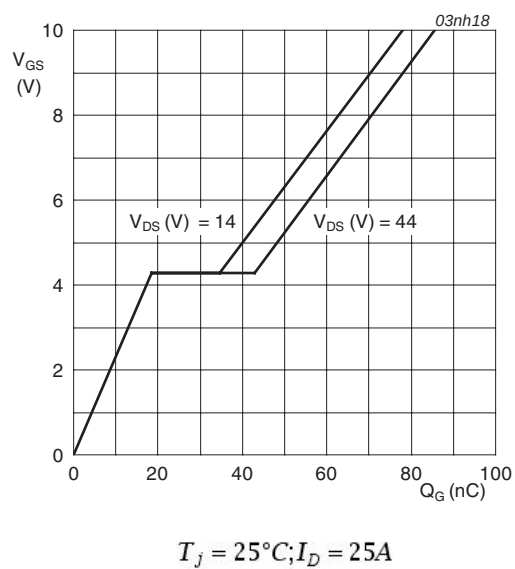
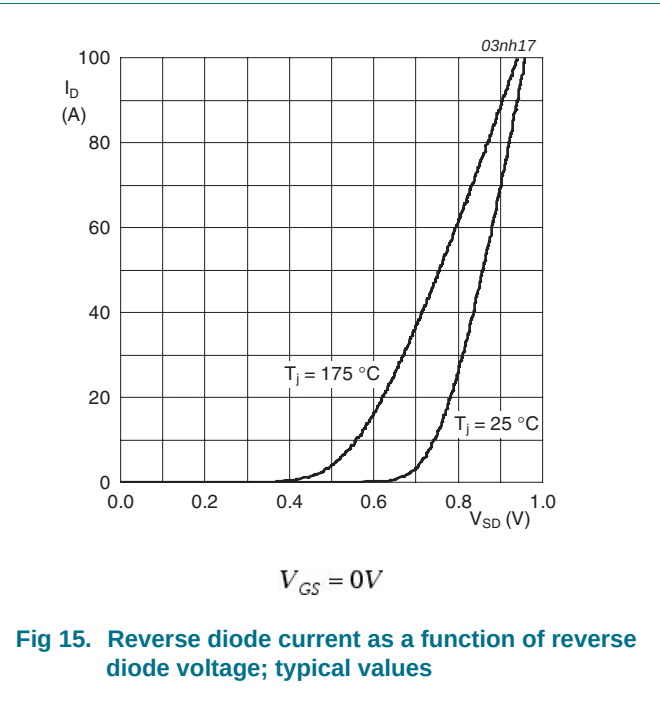
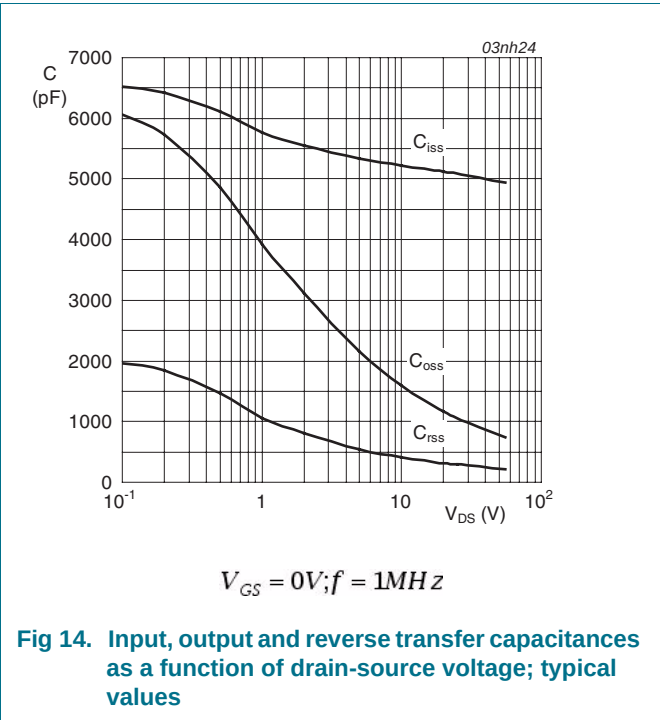


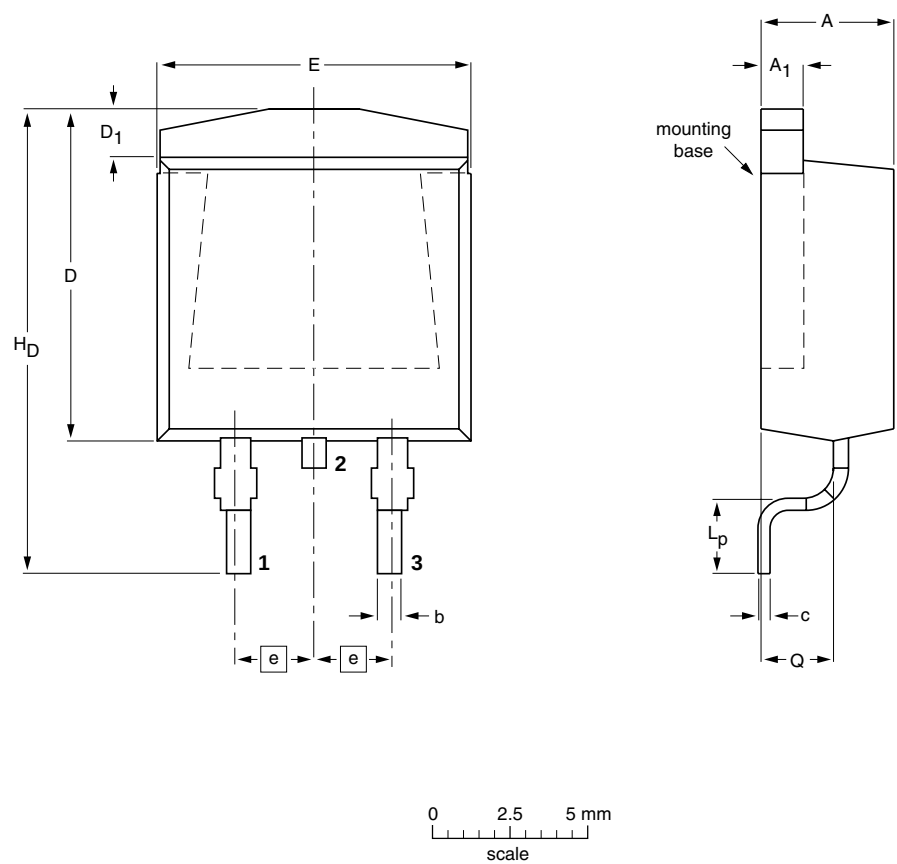
Fig 13. Gate-source voltage as a function of turn-on gate charge; typical values



7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	c	D _{max.}	D ₁	E	e	L _p	H _D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						05-02-11 06-03-16

Fig 16. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK764R0-55B v.5	20110422	Product data sheet	-	BUK75_764R0-55B_4
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number BUK764R0-55B separated from data sheet BUK75_764R0-55B_4.			
BUK75_764R0-55B_4	20071004	Product data sheet	-	BUK75_764R0-55B_3

9. Legal information

9.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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